

Intel[®] Q35/Q33, G35/G33/G31, P35/P31 Express Chipset Memory Technology and Configuration Guide

White Paper

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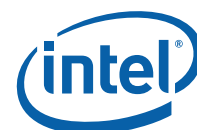
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Revision History

Revision Number	Description	Revision Date
-001	Initial release	May 2007
-002	Added Intel® Q35/Q33/G35/G31/P31 Express Chipset details	August 2007

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1 *Introduction*

This document details the Intel® Q35/Q33/G35/G33/G31/P35/P31 Express Chipset system memory technology enhancements, supported memory configurations, and memory organizations. It is intended for a technical audience interested in learning about the performance enhancements and simplified population rules offered by Intel® Fast Memory Access and Intel® Flex Memory Technology in the platforms based on the Intel Q35/Q33/G35/G33/G31/P35/P31 Express Chipset.



2 Technology Enhancements of Intel® Fast Memory Access (Intel® FMA)

This chapter details Intel® Q35/Q33/G35/G33/G31/P35/P31 Express Chipset technology enhancements of its memory controller known as Intel® Fast Memory Access (Intel® FMA).

With the growing reliance on faster and less latent memory technologies for today's high performance platforms, it has become necessary to not only increase system memory transfer rate speeds, but to also streamline usage of the memory controller protocol in novel and intelligent ways to decrease latency and optimize memory bandwidth. To do this, several Intel technologies, known collectively as Intel® FMA, have been included in this generation of Intel's chipsets.

The following sections outline and explain the technology enhancements: Just In Time Scheduling, Command Overlap, Out of Order Scheduling, and Opportunistic Writes.

2.1 Just in Time Command Scheduling

The Intel Q35/Q33/G35/G33/G31/P35/P31 Express Chipset has an advanced command scheduler where all pending requests are examined simultaneously to determine the most efficient request to be issued next. The most efficient request is picked from all pending requests and issued to system memory Just In Time to make optimal use of Command Overlapping. Thus, instead of having all memory access requests go individually through an arbitration mechanism forcing requests to be executed one at a time, they can be started without interfering with the current request allowing for concurrent issuing of requests. This allows for the optimization of bandwidth and reducing of latency while retaining system memory protocol.

2.2 Command Overlap

Command Overlap allows for the insertion of the DRAM commands between the Activate, Precharge, and Read/Write commands normally used, as long as the inserted commands do not affect the currently executing command. This allows for situations where multiple commands can be issued in an overlapping manner, increasing the efficiency of system memory protocol.



2.3 Out of Order Scheduling

Leveraging Just In Time Scheduling and Command Overlap, the Intel Q35/Q33/G35/G33/G31/P35/P31 Express Chipset continuously monitors pending requests to system memory for the best use of bandwidth and reduction of latency. If there are multiple requests to the same open page, these requests would be launched in a back to back manner to make optimum use of the open memory page. This ability to reorder requests on the fly allows the Intel Q35/Q33/G35/G33/G31/P35/P31 Express Chipset to further reduce latency and increase bandwidth efficiency. This is especially important for helping overcome the in-order manner of the Front Side Bus between the Intel Q35/Q33/G35/G33/G31/P35/P31 Express Chipset and the processor to minimize processor starvation.

2.4 Opportunistic Writes

Processor requests for memory reads usually are weighted more heavily than writes to memory to avoid cases of starving the processor of data to process while the writes are issued to system memory. Instead of having writes issued to a pending queue to be flushed to memory when certain watermarks are reached, which could starve the processor of data while it waits for the write flush to finish, the Intel Q35/Q33/G35/G33/G31/P35/P31 Express Chipset monitors system memory requests and issues pending write requests to memory at times when they will not impact memory read requests. This allows for an almost continuous flow of data to the processor for processing.



3 Supported Memory Technologies

3.1 Memory Technology Supported

The Q35/Q33/G35/G33/G31/P35/P31 Express Chipset supports the following DDR2 and DDR3 Data Transfer Rates, DIMM Modules, and DRAM Device Technologies:

- DDR2 Data Transfer Rates = 667 (PC2-5300) and 800 (PC2-6400)
- DDR3 Data Transfer Rates (G33/P35 Express Chipset Only) = 800 (PC3-6400) and 1067 (PC3-8500)
- DDR2 DIMM Modules:
 - Raw Card C - Single Sided x16 un-buffered non-ECC
 - Raw Card D - Single Sided x8 un-buffered non-ECC
 - Raw Card E - Double Sided x8 un-buffered non-ECC
- DDR3 DIMM Modules (G33/P35 Express Chipset Only):
 - Raw Card A - Single Sided x8 un-buffered non-ECC
 - Raw Card B - Double Sided x8 un-buffered non-ECC
 - Raw Card C - Single Sided x16 un-buffered non-ECC
 - Raw Card F - Double Sided x16 un-buffered non-ECC
- DDR2 and DDR3 (G33/P35 Express Chipset Only) DRAM Device Technology:
512 MB and 1 GB
 - Using 512 Mb device technologies, the smallest memory capacity possible is 256 MB, assuming Single Channel Mode with a single x16 single sided un-buffered non-ECC DIMM memory configuration.
 - Using 1 Gb device technologies, the largest memory capacity possible is 8 GB, assuming Dual Channel Mode with four x8 double sided un-buffered non-ECC DIMM memory configuration.



Table 3-1. Memory Technology Support Details

Mem. Type	Raw Card Ver.	DIMM Cap.	DRAM Device Tech.	DRAM Org.	# of DRAM Devices	# of Physical Device Ranks	# of Row /Col Address Bits	# of Banks Inside DRAM	Page Size
DDR2 667 and 800	C	256 MB	512 MB	32M X 16	4	1	13/10	4	8K
		512 MB	1 GB	64M X 16	4	1	13/10	8	8K
	D	512 MB	512 MB	64M X 8	8	1	14/10	4	8K
		1 GB	1 GB	128M X 8	8	1	14/10	8	8K
	E	1 GB	512 MB	64M X 8	16	2	14/10	4	8K
		2 GB	1 GB	128M X 8	16	2	14/10	8	8K
DDR3 800 and 1067 (G33/ P35 Only)	A	512 MB	512 MB	64M X 8	8	1	13/10	8	8K
		1 GB	1 GB	128M X 8	8	1	14/10	8	8K
	B	1 GB	512 MB	64M X 8	16	2	13/10	8	8K
		2 GB	1 GB	128M X 8	16	2	14/10	8	8K
	C	256 MB	512 MB	32M X 16	4	1	12/10	8	8K
		512 MB	1 GB	64M X 16	4	1	13/10	8	8K
	F	512 MB	512 MB	32M X 16	8	2	12/10	8	8K
		1 GB	1 GB	64M X 16	8	2	13/10	8	8K

3.2 DRAM Device Timing Support

The Q35/Q33/G35/G33/G31/P35/P31 Express Chipset supports the following DDR2 and DDR3 DRAM Device Speed Bin and Write Latency (WL) Timings on the main memory interface.

Table 3-2. DDR2 and DDR3 DRAM Device Timing Support

Memory Type	DRAM Data Rate	t _{CL}	t _{RCD}	t _{RP}	WL	Units
DDR2	667 MT/s	5	5	5	4	tCK
	800 MT/s	5	5	5	4	tCK
	800 MT/s	6	6	6	5	tCK
DDR3 (G33/P35 Only)	800 MT/s	5	5	5	5	tCK
	800 MT/s	6	6	6	5	tCK
	1067 MT/s	7	7	7	6	tCK
	1067 MT/s	8	8	8	6	tCK



3.3 ECC Support

The Q35/Q33/G35/G33/G31/P35/P31 Express Chipset does **NOT** support ECC, does not support ECC un-buffered DIMMs, and it does not support any memory configuration that mixes non-ECC with ECC un-buffered DIMMs. See Section 3.1 for un-buffered DIMM support details.

3.4 Valid Front Side Bus and Memory Speeds

The Q35/Q33/G35/G33/G31/P35/P31 Express Chipset supports the following Front Side Bus (FSB) and system memory speed configurations.

Table 3-3. Intel® Q35/Q33/G35/G33/G31/P35/P31 Valid FSB/Memory Speed Configurations

Memory Type	Express Chipset	FSB	DRAM Data Rate	Single Channel Peak Bandwidth	Dual Channel Peak Bandwidth
DDR2	Q35, Q33, G35, G33, P35	1333 MHz	800 MT/s	6.4 GB/s	12.8 GB/s
		1333 MHz	667 MT/s	5.3 GB/s	10.6 GB/s
	Q35, Q33, G35, G33, P35, G31, P31	1067 MHz	800 MT/s	6.4 GB/s	12.8 GB/s
		1067 MHz	667 MT/s	5.3 GB/s	10.6 GB/s
		800 MHz	800 MT/s	6.4 GB/s	12.8 GB/s
		800 MHz	667 MT/s	5.3 GB/s	10.6 GB/s
DDR3	G33 and P35	1333 MHz	1067 MT/s	8.5 GB/s	17.0 GB/s
		1333 MHz	800 MT/s	6.4 GB/s	12.8 GB/s
		1067 MHz	1067 MT/s	8.5 GB/s	17.0 GB/s
		1067 MHz	800 MT/s	6.4 GB/s	12.8 GB/s
		800 MHz	800 MT/s	6.4 GB/s	12.8 GB/s

Note: The Q35/Q33/G35/G33/G31/P35/P31 Express Chipset does not support system memory frequencies that exceed the frequency of the Front Side Bus. If memory with higher frequency capabilities than that of the FSB is populated, the memory will be under-clocked to align with the FSB.

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4 Memory Organization and Operating Modes

The Intel Q35/Q33/G35/G33/G31/P35/P31 Express Chipset memory interface is designed with Intel® Flex Memory Technology so that it can be configured to support single-channel or dual-channel DDR2 or DDR3 memory configurations. Depending upon how the DIMMs are populated in each memory channel, a number of different configurations can exist for DDR2 or DDR3.

The following sections explain and show the different memory configurations that are supported by the Q35/Q33/G35/G33/G31/P35/P31 Express Chipset.

4.1 Single-Channel Mode

In this mode, all memory cycles are directed to a single channel.

Single channel mode is used when either Channel-0 or Channel-1 DIMMs are populated in any order, but not both.

4.2 Dual Channel Modes

4.2.1 Dual Channel Symmetric Mode

This mode provides maximum performance on real applications. Addresses are ping-ponged between the channels after each cache line (64 byte boundary). If there are two requests, and the second request is to an address on the opposite channel from the first, that request can be sent before data from the first request has returned. If two consecutive cache lines are requested, both may be retrieved simultaneously, since they are ensured to be on opposite channels.

Dual channel symmetric mode is used when both Channel-0 and Channel-1 DIMMs are populated in any order with the total amount of memory in each channel being the same, but the DRAM device technology and width may vary from one channel to the other.

Table 4-1 is a sample dual channel symmetric memory configuration showing the rank organization.



Table 4-1. Sample Dual Channel Symmetric Organization Mode

Rank	Channel 0 Population	Cumulative Top Address in Channel 0	Channel 1 Population	Cumulative Top Address in Channel 1
Rank 3	0 MB	2560 MB	0 MB	2560 MB
Rank 2	256 MB	2560 MB	256 MB	2560 MB
Rank 1	512 MB	2048 MB	512 MB	2048 MB
Rank 0	512 MB	1024 MB	512 MB	1024 MB

4.2.2 Dual Channel Asymmetric Modes

4.2.2.1 Stacked Asymmetric Mode

In this addressing mode addresses start in channel-0 and stay there until the end of the highest rank in channel-0, and then addresses continue from the bottom of channel-1 to the top.

This mode is used when both Channel-0 and Channel-1 DIMMs are populated in any order with the total amount of memory in each channel being different.

Table 4-2 is a sample dual channel stacked asymmetric memory configuration showing the rank organization.

Table 4-2. Sample Dual Channel Stacked Asymmetric Organization Mode

Rank	Channel 0 Population	Cumulative Top Address in Channel 0	Channel 1 Population	Cumulative Top Address in Channel 1
Rank 3	0 MB	1280 MB	0 MB	2304 MB
Rank 2	256 MB	1280 MB	0 MB	2304 MB
Rank 1	512 MB	1024 MB	512 MB	2304 MB
Rank 0	512 MB	512 MB	512 MB	1792 MB



4.2.2.2 L-shaped Asymmetric Mode

In this addressing mode the lowest DRAM memory is mapped to dual channel operation and the top most DRAM memory is mapped to single channel operation. In this mode the system can run at one zone of dual channel mode and one zone of single channel mode simultaneously across the whole memory array.

This mode is used when both Channel-0 and Channel-1 DIMMs are populated in any order with the total amount of memory in each channel being different.

Table 4-3 is a sample dual channel L-shaped asymmetric memory configuration showing the rank organization.

Table 4-3. Sample Dual Channel L-Shaped Asymmetric Organization Mode

Rank	Channel 0 Population	Cumulative Top Address in Channel 0	Channel 1 Population	Cumulative Top Address in Channel 1
Rank 3	0 MB	2048 MB	0 MB	2304 MB
Rank 2	0 MB	2048 MB	256 MB	2304 MB
Rank 1	512 MB	2048 MB	512 MB	2048 MB
Rank 0	512 MB	1024 MB	512 MB	1024 MB

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